



PMV15UNEA

20 V, N-channel Trench MOSFET

6 September 2019

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Extended temperature range $T_j = 175\text{ °C}$
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 500 V HBM (class H1B)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

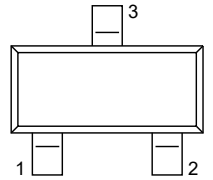
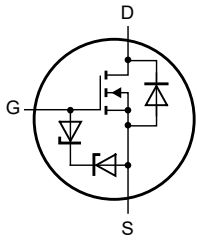
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	-	20	V
V_{GS}	gate-source voltage		-8	-	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	7	A
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 7\text{ A}; T_j = 25\text{ °C}$	-	15	19	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV15UNEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMV15UNEA	%GN

[1] % = placeholder for manufacturing site code

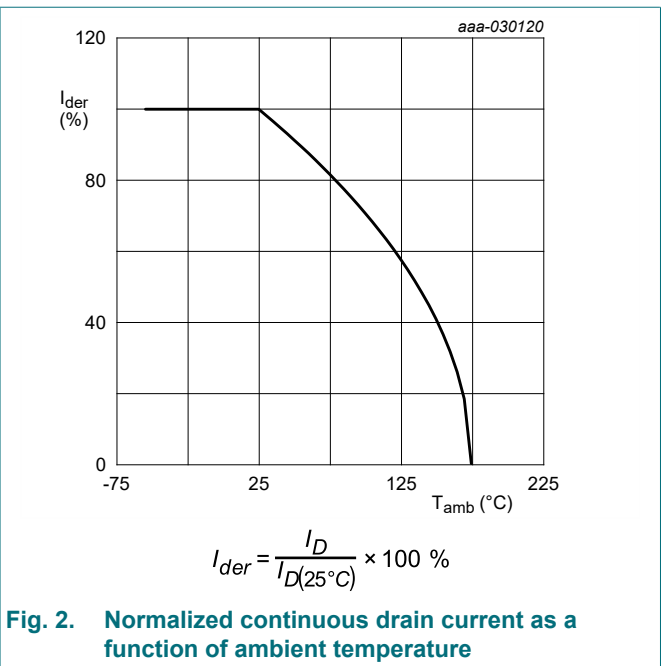
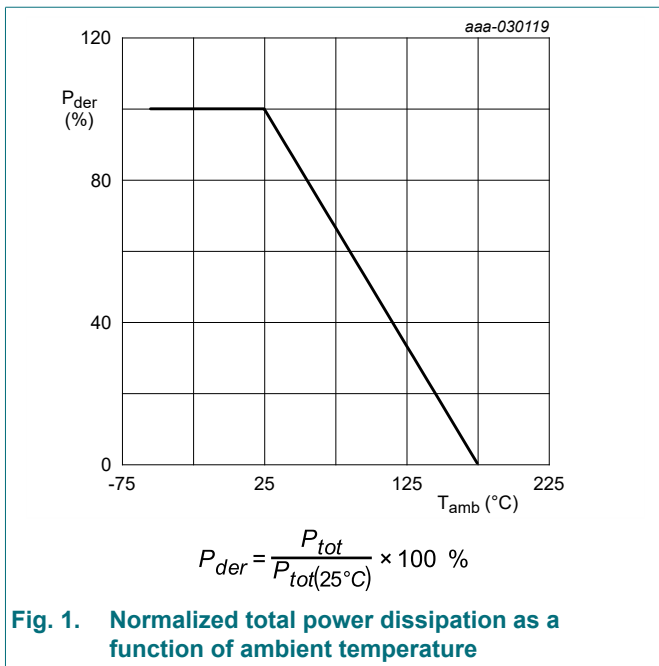
8. Limiting values

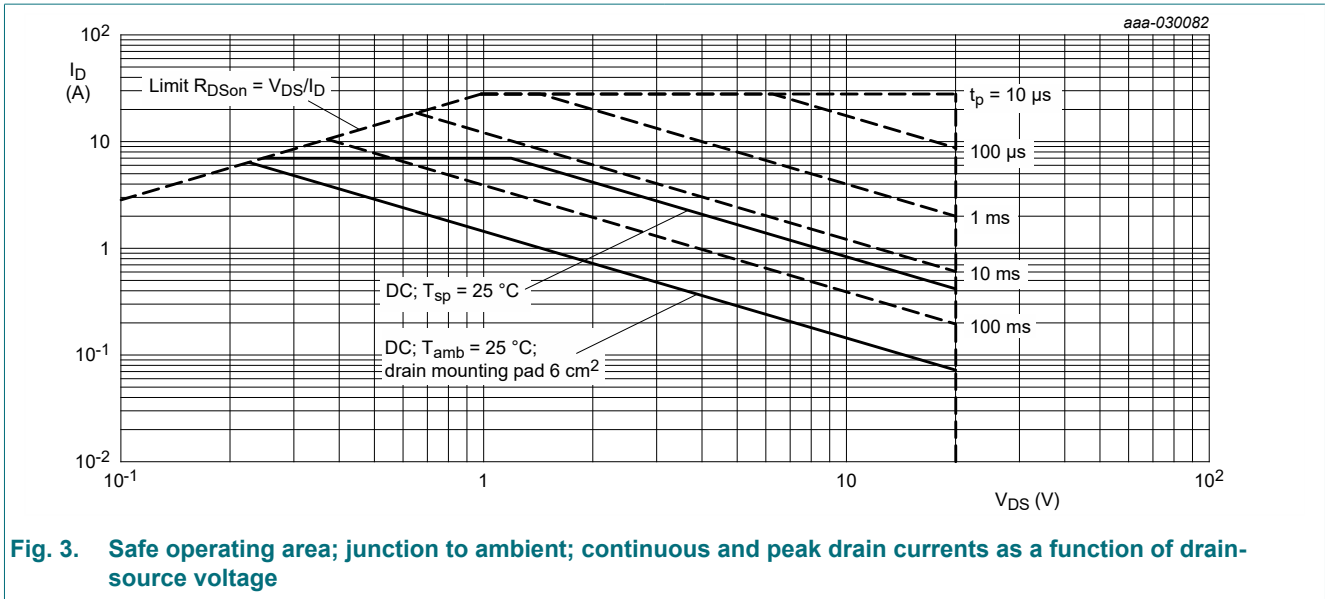
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	7	A
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	4.4	A
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	28	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	610	mW
			[1]	-	1.4	W
		T _{sp} = 25 °C		-	8.3	W
T _j	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	1.4	A
ESD maximum rating						
V _{ESD}	electrostatic discharge voltage	HBM	[3]	-	500	V
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	T _{j(initial)} = 25 °C; I _D = 1.5 A; DUT in avalanche (unclamped)		-	14	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.





9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	208	245	K/W
			[2]	-	88	104	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	13	18	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

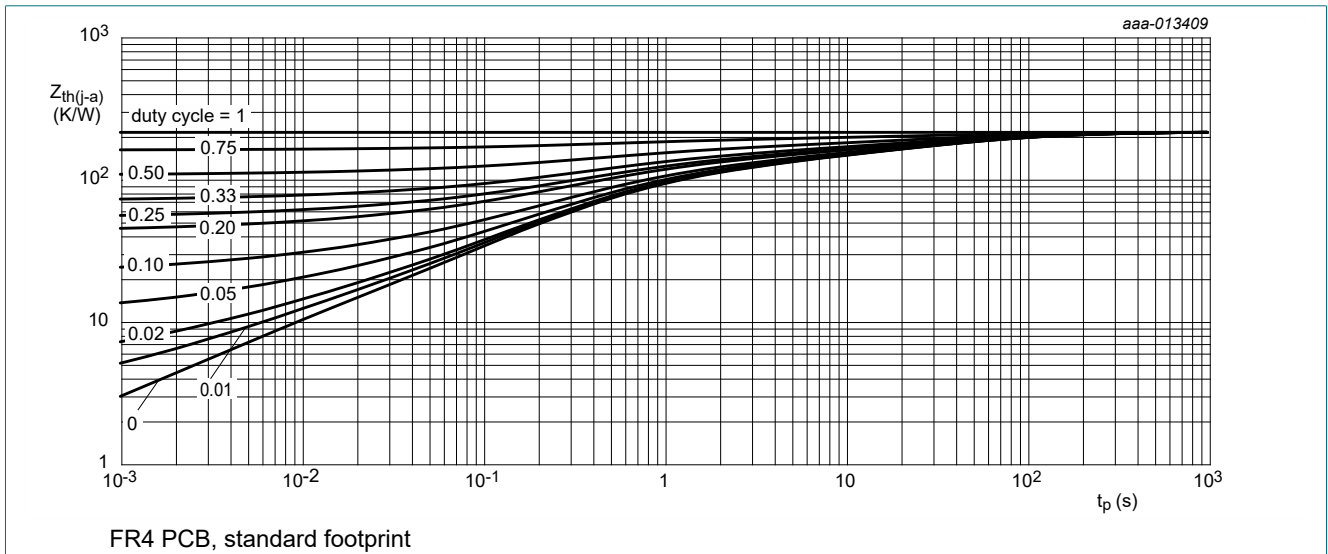


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

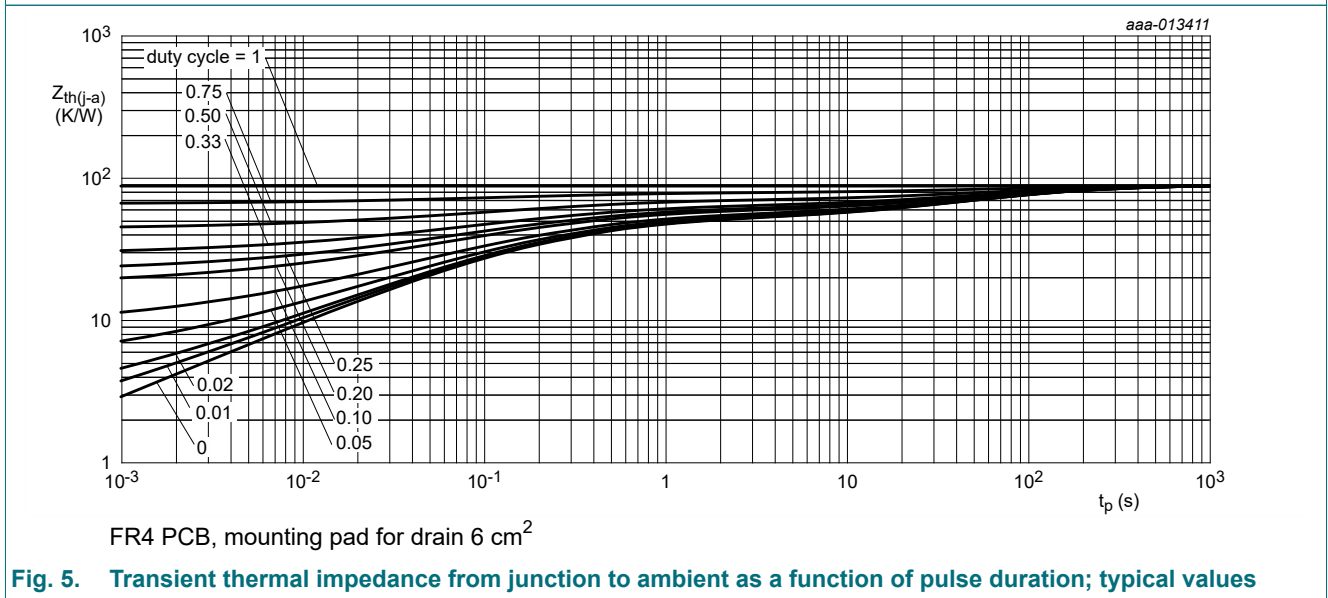


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ C$	0.4	0.65	0.9	V
I_{DSS}	drain leakage current	$V_{DS} = 20 V$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	1	μA
I_{GSS}	gate leakage current	$V_{GS} = 8 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	10	μA
		$V_{GS} = -8 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	-	-10	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 V$; $I_D = 7 A$; $T_j = 25 \text{ }^\circ C$	-	15	19	m Ω
		$V_{GS} = 4.5 V$; $I_D = 7 A$; $T_j = 175 \text{ }^\circ C$	-	28	35	m Ω
		$V_{GS} = 2.5 V$; $I_D = 5.7 A$; $T_j = 25 \text{ }^\circ C$	-	18	24	m Ω
		$V_{GS} = 1.8 V$; $I_D = 2 A$; $T_j = 25 \text{ }^\circ C$	-	23	36	m Ω
g_{fs}	forward transconductance	$V_{DS} = 10 V$; $I_D = 7 A$; $T_j = 25 \text{ }^\circ C$	-	50	-	S
R_G	gate resistance	$f = 1 \text{ MHz}$	-	2	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10 V$; $I_D = 6 A$; $V_{GS} = 4.5 V$; $T_j = 25 \text{ }^\circ C$	-	11	17	nC
Q_{GS}	gate-source charge		-	1.3	-	nC
Q_{GD}	gate-drain charge		-	2.1	-	nC
C_{iss}	input capacitance	$V_{DS} = 10 V$; $f = 1 \text{ MHz}$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	1220	-	pF
C_{oss}	output capacitance		-	124	-	pF
C_{rss}	reverse transfer capacitance		-	102	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 10 V$; $I_D = 6 A$; $V_{GS} = 4.5 V$; $R_{G(ext)} = 6 \Omega$; $T_j = 25 \text{ }^\circ C$	-	10	-	ns
t_r	rise time		-	24	-	ns
$t_{d(off)}$	turn-off delay time		-	32	-	ns
t_f	fall time		-	34	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 1.4 A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ C$	-	0.7	1.2	V
t_{rr}	reverse recovery time	$I_S = 1.5 A$; $di_S/dt = -100 A/\mu s$;	-	10	-	ns
Q_r	recovered charge	$V_{GS} = 0 V$; $V_{DS} = 10 V$; $T_j = 25 \text{ }^\circ C$	-	2	-	nC

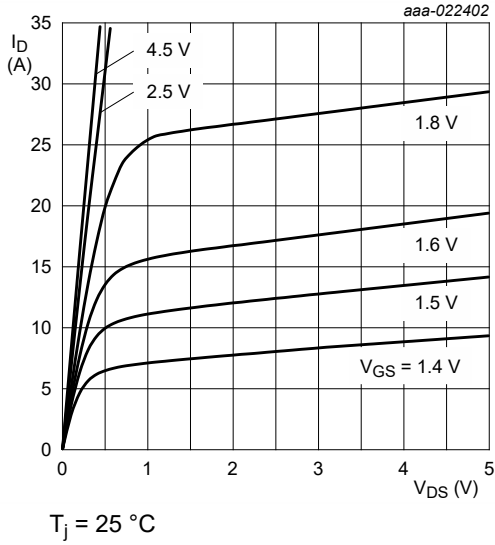


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

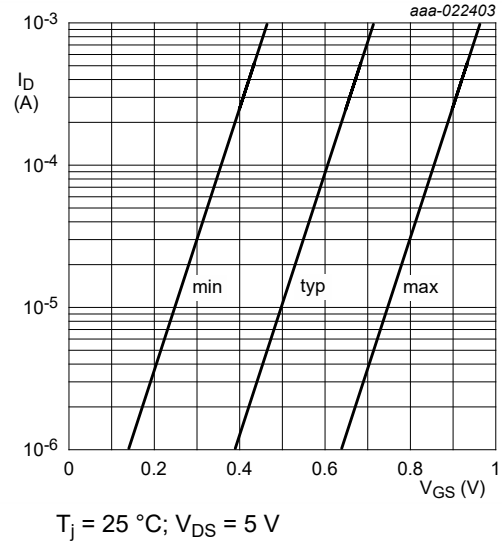


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

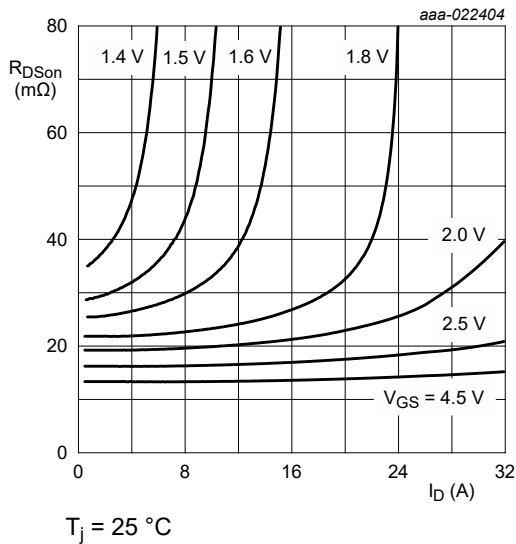


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

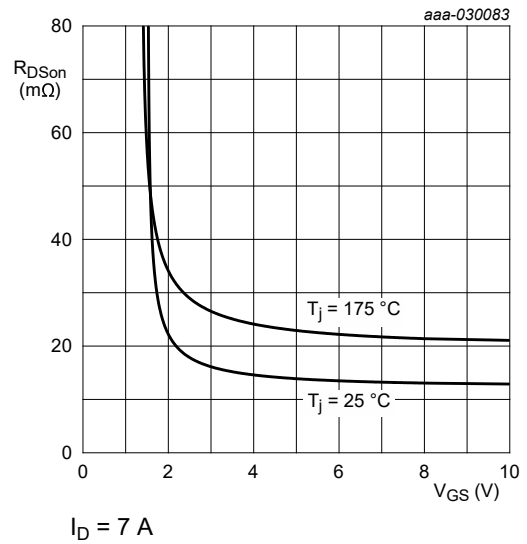
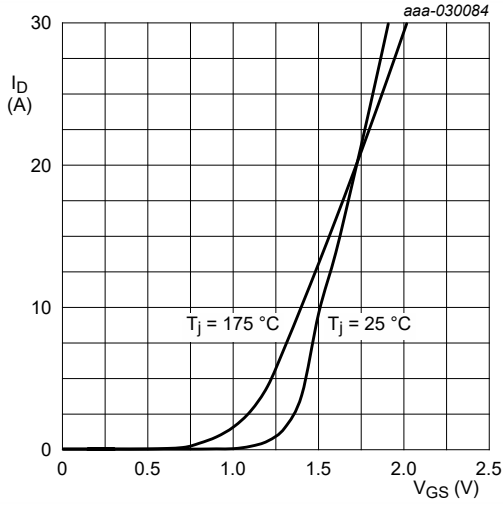
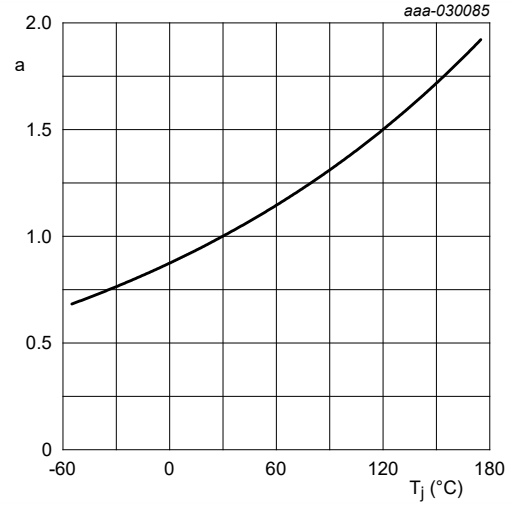


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



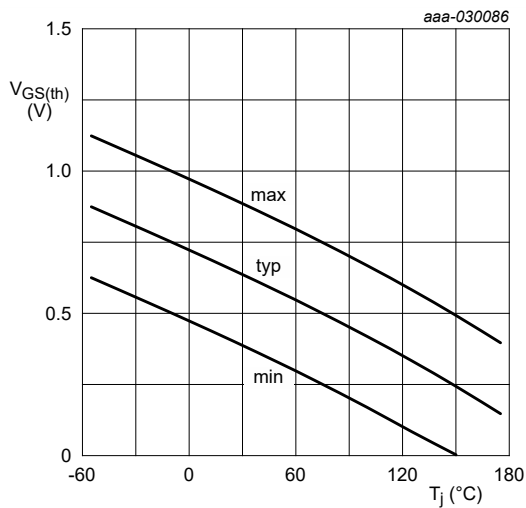
$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



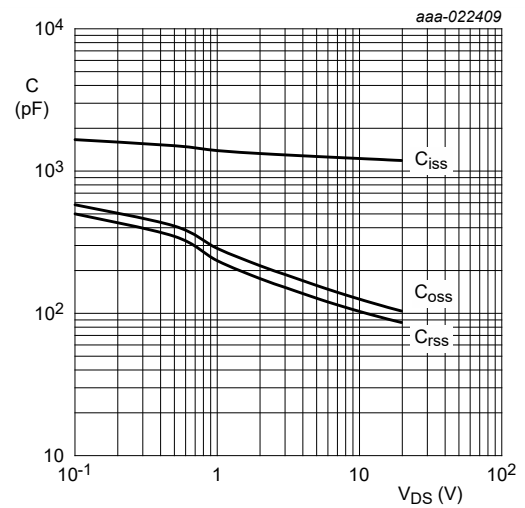
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



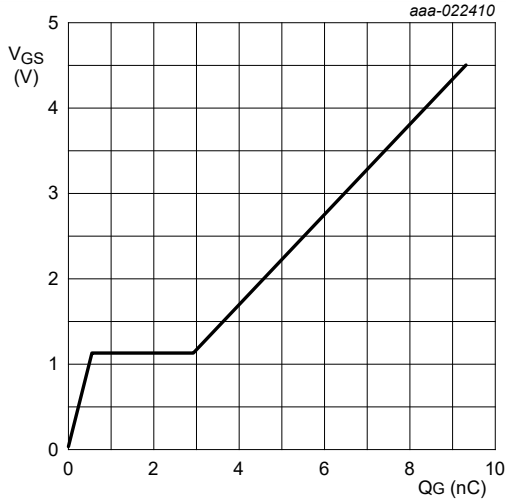
$$I_D = 250 \mu A; V_{DS} = V_{GS}$$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 6 \text{ A}; V_{DS} = 10 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

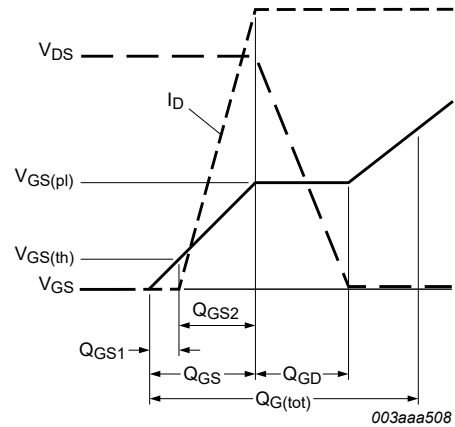
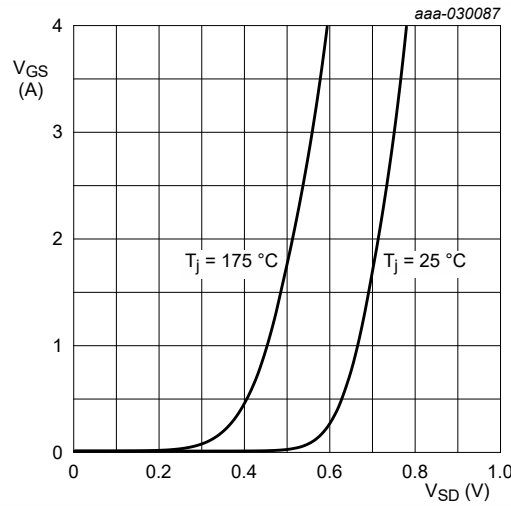


Fig. 15. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

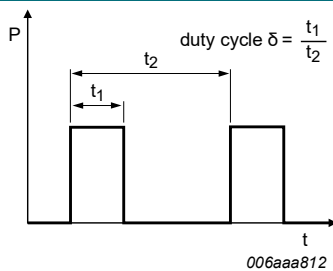


Fig. 17. Duty cycle definition

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

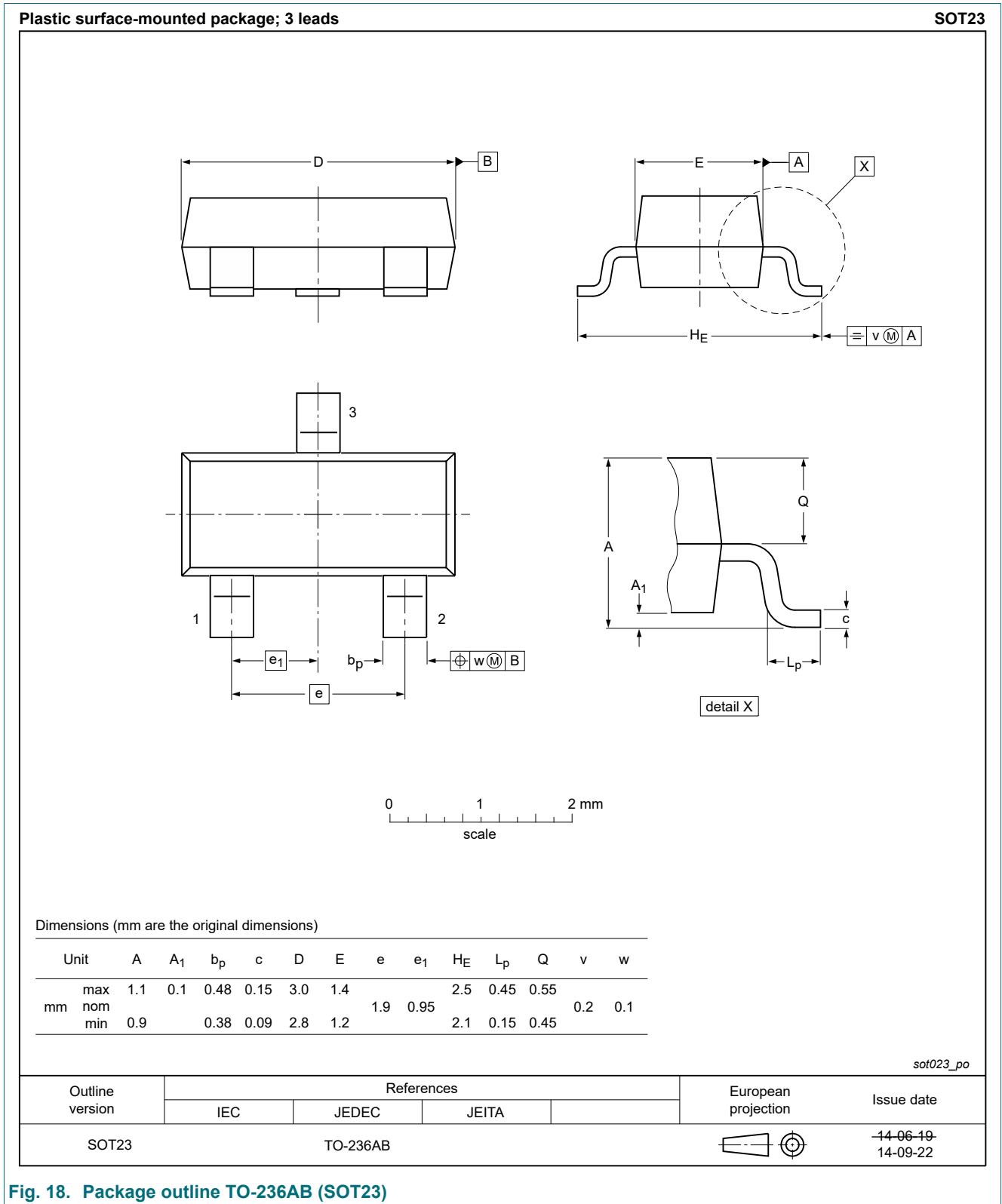


Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering

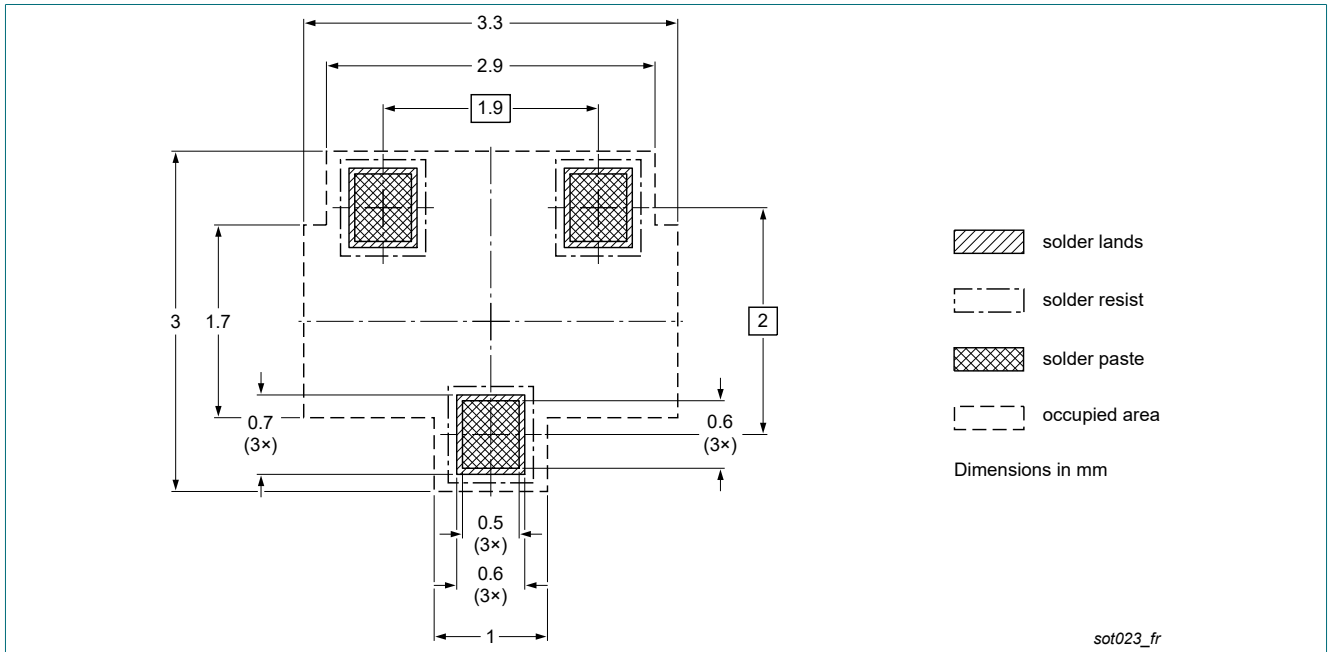


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

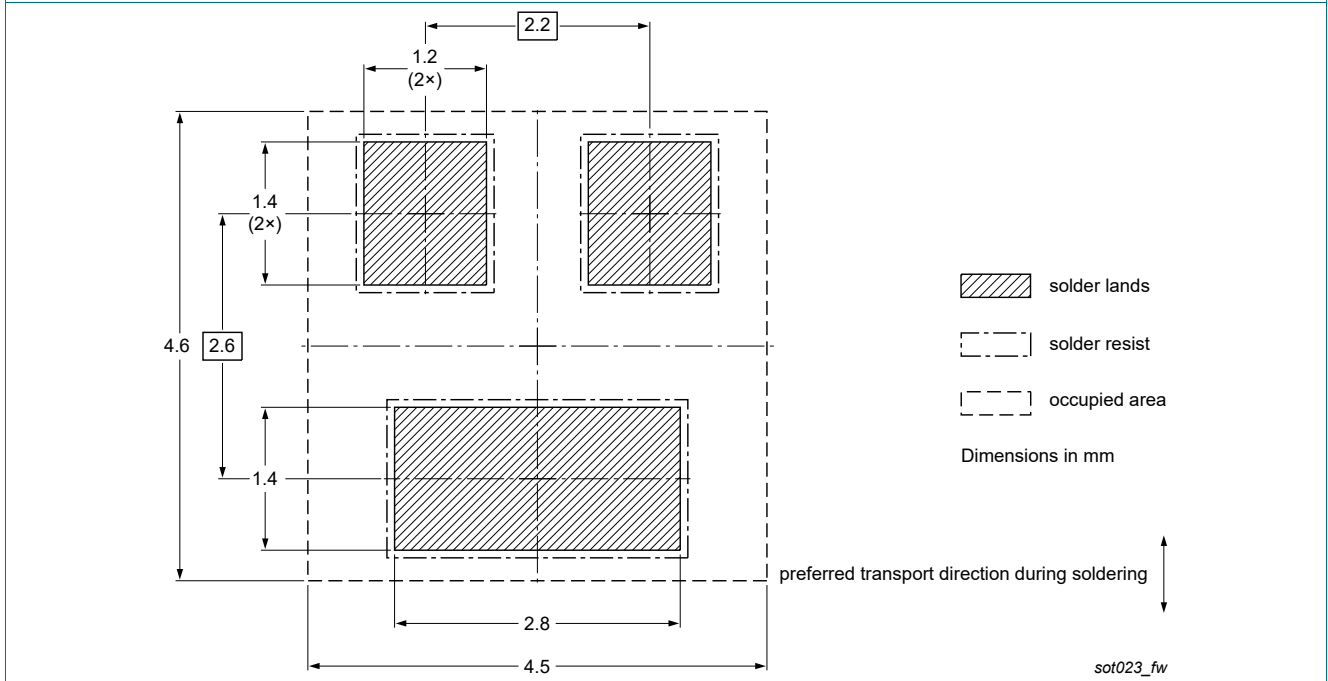


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV15UNEA v.1	20190906	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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